



SiC - photodiode JEC 0,1-4L

**characteristics :**

- ◆ spectral range 210 ... 380 nm
- ◆ active area 0,055 mm²
- ◆ high UV - response 0,13 A/W
- ◆ TO 39-package
- ◆ lensecap
- ◆ components are in conformity with RoHS and WEEE

applications :

- ◆ UV-measurement only
- ◆ UV-source control (for instance in sterilizers)
- ◆ flamedetection

maximum ratings:

maximum reverse voltage	20	V
operating temperature range	- 25 °C ... 70	°C
storage temperature range	- 40 °C ... 100	°C
soldering temperature (3s)	260	°C

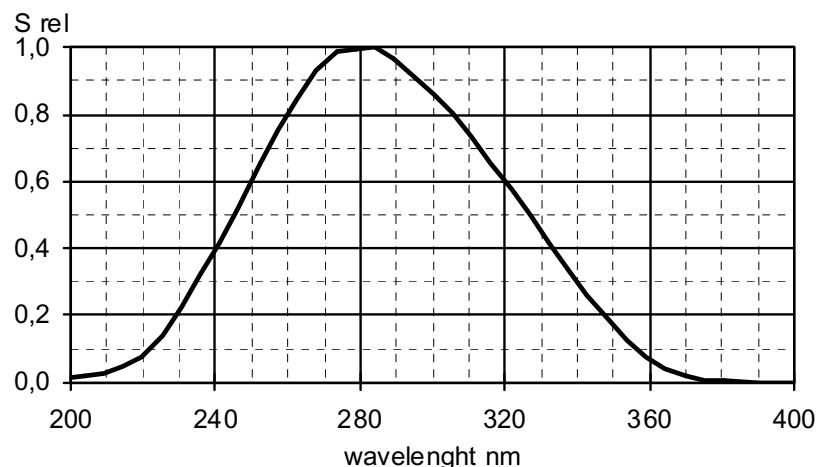
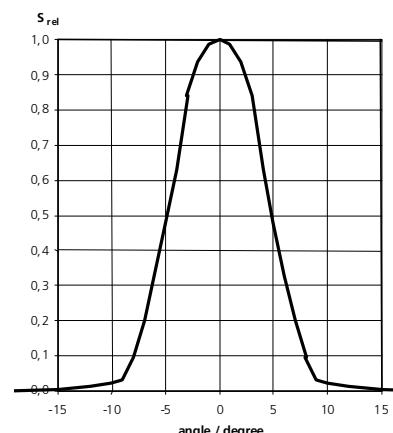
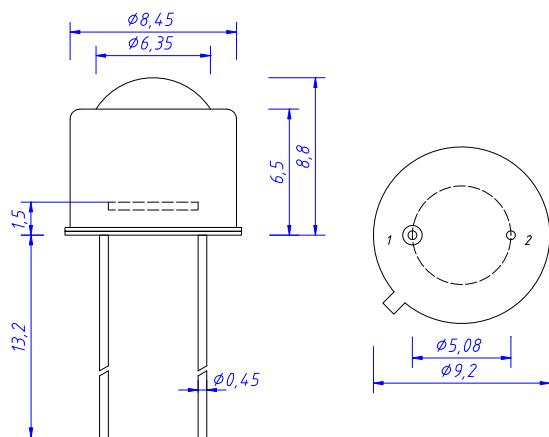
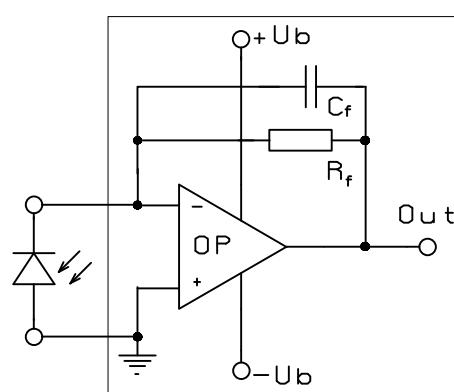
technical data :

test conditions, as not otherwise specified: $\gamma_a = 25 \text{ }^{\circ}\text{C}$, $V_R = 0\text{V}$

parameters	test conditions	min.	typ.	max.	unit
active area ¹⁾			2,75		mm ²
spectral range		210		380	nm
maximum of spectral responsivity	$\lambda_{max} = 275 \text{ nm}$		0,13		A/W
absolute spectral responsivity	$\lambda = 254 \text{ nm}$		0,11		A/W
dark current I_R	$V_R = 1 \text{ V}$		1		fA
short current	bright sun		50		nA
(sunlight)	cloudy		20		
capacitance			21		pF

¹⁾ effektive active area because of focusing of light by the lens

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relative spectral response**response characteristic****package dimensions****application example**

1 Kathode

2 Anode & Case

The application example shows a typical circuit. R_f is responsible for the gain of the circuit. C_f compensates the reverse junction capacitance of the photodiode and input capacitance of the OPV. The exact value of C_f depends on R_f , used OPV and capacitance of the circuit. A typical value is 1 pF.

The diagram shows dependence of amplitude of the application circuit with AD795, $R_f = 50 \text{ M}\Omega$ and $C_f = 0.5 \text{ pF}$.

Gain in db

